

Fig. 8 is a cross-sectional view of a semiconductor device. It shows a substrate 801 with a p-type region 802 and n-type regions 803. A SiO₂ layer 804 is on top, with a patterned layer 805 and a contact layer 806. A gate structure 807 is shown on the left, and a contact pad 808 is on the right.

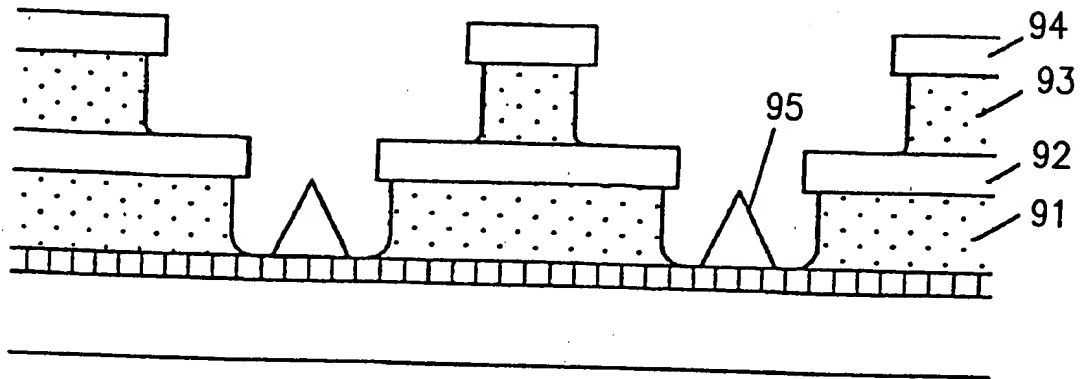
FIG. 8

The diagram shows a transistor amplifier circuit. A transistor 803 (E) has its base connected to a voltage divider consisting of resistors 806 and 807, which is biased by a voltage source 812 (V_g). The emitter of the transistor is connected to ground through a resistor 810. The collector is connected to a load resistor 808, which is in turn connected to a DC supply 814 (V_{gs}). A feedback path is provided by a resistor 809 (A) connected between the collector and the base. A current source, represented by a circle with an arrow and labeled 1A, is connected in series with the collector load resistor 808. A voltage source 813 (V_a) is connected in series with the current source. Ground connections are indicated by three horizontal lines at the bottom of the circuit.

PRIOR ART

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FIG. 9



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